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(12) **United States Patent**
Qian et al.(10) **Patent No.:** **US 9,144,880 B2**
(45) **Date of Patent:** ***Sep. 29, 2015**(54) **SOFT AND CONDITIONABLE CHEMICAL MECHANICAL POLISHING PAD**(71) Applicant: **Rohm and Haas Electronic Materials CMP Holdings, Inc.**, Newark, DE (US)(72) Inventors: **Bainian Qian**, Newark, DE (US); **David B. James**, Newark, DE (US); **James Murnane**, Norristown, PA (US); **Fengji Yeh**, Wilmington, DE (US); **Marty W. DeGroot**, Middletown, DE (US)(73) Assignee: **Rohm and Haas Electronic Materials CMP Holdings, Inc.**, Newark, DE (US)

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B24D 11/00 (2006.01)(52) **U.S. Cl.**CPC .. **B24B 37/24** (2013.01); **C09G 1/02** (2013.01)(58) **Field of Classification Search**CPC C08L 2312/00; C09G 1/00; C09G 1/02; C09K 3/1463; B24D 11/00; B24B 53/017
See application file for complete search history.(56) **References Cited**

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(57) **ABSTRACT**

A chemical mechanical polishing pad for polishing a substrate selected from at least one of a magnetic substrate, an optical substrate and a semiconductor substrate is provided containing a polishing layer, wherein the polishing layer comprises the reaction product of raw material ingredients, including: a polyfunctional isocyanate; and, a curative package; wherein the curative package contains an amine initiated polyol curative and a high molecular weight polyol curative; wherein the polishing layer exhibits a density of greater than 0.6 g/cm³; a Shore D hardness of 5 to 40; an elongation to break of 100 to 450%; and, a cut rate of 25 to 150 μm/hr; and, wherein the polishing layer has a polishing surface adapted for polishing the substrate. Also provide are methods of making and using the chemical mechanical polishing pad.

14 Claims, No Drawings

SOFT AND CONDITIONABLE CHEMICAL MECHANICAL POLISHING PAD

The present invention relates to chemical mechanical polishing pads and methods of making and using the same. More particularly, the present invention relates to a chemical mechanical polishing pad comprising a polishing layer, wherein the polishing layer exhibits a density of greater than 0.6 g/cm³; a Shore D hardness of 5 to 40; an elongation to break of 100 to 450%; and, a cut rate of 25 to 150 μm/hr; and, wherein the polishing layer has a polishing surface adapted for polishing the substrate.

In the fabrication of integrated circuits and other electronic devices, multiple layers of conducting, semiconducting and dielectric materials are deposited onto and removed from a surface of a semiconductor wafer. Thin layers of conducting, semiconducting and dielectric materials may be deposited using a number of deposition techniques. Common deposition techniques in modern wafer processing include physical vapor deposition (PVD), also known as sputtering, chemical vapor deposition (CVD), plasma-enhanced chemical vapor deposition (PECVD) and electrochemical plating, among others. Common removal techniques include wet and dry isotropic and anisotropic etching, among others.

As layers of materials are sequentially deposited and removed, the uppermost surface of the wafer becomes non-planar. Because subsequent semiconductor processing (e.g., metallization) requires the wafer to have a flat surface, the wafer needs to be planarized. Planarization is useful for removing undesired surface topography and surface defects, such as rough surfaces, agglomerated materials, crystal lattice damage, scratches and contaminated layers or materials.

Chemical mechanical planarization, or chemical mechanical polishing (CMP), is a common technique used to planarize or polish work pieces such as semiconductor wafers. In conventional CMP, a wafer carrier, or polishing head, is mounted on a carrier assembly. The polishing head holds the wafer and positions the wafer in contact with a polishing layer of a polishing pad that is mounted on a table or platen within a CMP apparatus. The carrier assembly provides a controllable pressure between the wafer and polishing pad. Simultaneously, a polishing medium (e.g., slurry) is dispensed onto the polishing pad and is drawn into the gap between the wafer and polishing layer. To effect polishing, the polishing pad and wafer typically rotate relative to one another. As the polishing pad rotates beneath the wafer, the wafer sweeps out a typically annular polishing track, or polishing region, wherein the wafer's surface directly confronts the polishing layer. The wafer surface is polished and made planar by chemical and mechanical action of the polishing layer and polishing medium on the surface.

Pad surface "conditioning" or "dressing" is critical to maintain a consistent polishing surface for stable polishing performance. Over time the polishing surface of the polishing pad wears down, smoothing over the microtexture of the polishing surface—a phenomenon called "glazing". Polishing pad conditioning is typically achieved by abrading the polishing surface mechanically with a conditioning disk. The conditioning disk has a rough conditioning surface typically comprised of embedded diamond points. The conditioning disk is brought into contact with the polishing surface either during intermittent breaks in the CMP process when polishing is paused ("ex situ"), or while the CMP process is underway ("in situ"). Typically the conditioning disk is rotated in a position that is fixed with respect to the axis of rotation of the polishing pad, and sweeps out an annular conditioning region as the polishing pad is rotated. The conditioning process as

described cuts microscopic furrows into the pad surface, both abrading and plowing the pad material and renewing the polishing texture.

Semiconductor devices are becoming increasingly complex with finer features and more metallization layers. This trend requires improved performance from polishing consumables in order to maintain planarity and limit polishing defects. The latter can create electrical breaks or shorts of the conducting lines that would render the semiconductor device non-functional. It is generally known that one approach to reduce polishing defects, such as micro-scratches or chatter marks, is to use a softer polishing pad.

A family of soft polyurethane polishing layers are disclosed by James, et al. in U.S. Pat. No. 7,074,115. James et al. discloses a polishing pad comprising a the reaction product of an isocyanate-terminated urethane prepolymer with an aromatic diamine or polyamine curative, wherein the reaction product exhibits a porosity of at least 0.1 volume percent, a KEL energy loss factor at 40° C. and a 1 rad/sec of 385 to 750 l/Pa, and a modulus E' at 40° C. and 1 rad/sec of 100 to 400 MPa.

As described above, it is necessary to diamond condition the surface of chemical mechanical polishing pads to create a favorable microtexture for optimum polishing performance. However, it is difficult to create such texture in conventional polishing layer materials, such as those described by James et al., because these materials exhibit a high ductility, as measured by tensile elongation to break values. As a result, when these materials are subjected to conditioning with a diamond conditioning disk, rather than cutting furrows into the pad's surface, the diamonds in the conditioning disk simply push the pad material aside without cutting. Hence, very little texture is created in the surface of these conventional materials as a result of conditioning with a diamond conditioning disk.

Another related problem with these conventional chemical mechanical polishing pad materials arises during the machining process to form macro groove patterns in the pad surface. Conventional chemical mechanical polishing pads are typically provided with a groove pattern cut into their polishing surface to promote slurry flow and to remove polishing debris from the pad-wafer interface. Such grooves are frequently cut into the polishing surface of the polishing pad either using a lathe or by a CNC milling machine. With soft pad materials, however, a similar problem to that of diamond conditioning occurs, such that after the cutting bit has passed, the pad material simply rebounds and the grooves formed close in on themselves. Thus groove quality is poor and it is more difficult to successfully manufacture commercially acceptable pads with such soft materials. This problem worsens as the hardness of the pad material decreases.

Accordingly, there is a continuing need for chemical mechanical polishing pads that provide a physical property profile that correlates well with that associated with low defect formulations, but which also imparts enhanced conditionability to the polishing layer (i.e., exhibits a cut rate of 25 to 150 μm/hr).

The present invention provides a chemical mechanical polishing pad for polishing a substrate selected from at least one of a magnetic substrate, an optical substrate and a semiconductor substrate; comprising a polishing layer, wherein the polishing layer comprises the reaction product of raw material ingredients, comprising: a polyfunctional isocyanate; and, a curative package, comprising: at least 5 wt % of an amine initiated polyol curative, wherein the amine initiated polyol curative contains at least one nitrogen atom per molecule; wherein the amine initiated polyol curative has an

average of at least three hydroxyl groups per molecule; 25 to 95 wt % of a high molecular weight polyol curative, wherein the high molecular weight polyol curative has a number average molecular weight, M_n , of 2,500 to 100,000; and wherein the high molecular weight polyol curative has an average of 3 to 10 hydroxyl groups per molecule; and, 0 to 70 wt % of a difunctional curative; wherein the polishing layer exhibits a density of ≥ 0.6 g/cm³; a Shore D hardness of 5 to 40; an elongation to break of 100 to 450%; and, a cut rate of 25 to 150 μ m/hr; and, wherein the polishing layer has a polishing surface adapted for polishing the substrate.

The present invention provides a chemical mechanical polishing pad for polishing a substrate selected from at least one of a magnetic substrate, an optical substrate and a semiconductor substrate; comprising a polishing layer, wherein the polishing layer comprises the reaction product of raw material ingredients, comprising: a polyfunctional isocyanate; and, a curative package, comprising: 5 to 20 wt % of the amine initiated polyol curative, wherein the amine initiated polyol curative contains two nitrogen atom per molecule; wherein the amine initiated polyol curative has an average of 4 hydroxyl groups per molecule; and, wherein the amine initiated polyol curative has a number average molecular weight, M_n , of 200 to 400; 50 to 75 wt % of the high molecular weight polyol curative, wherein the high molecular weight polyol curative has a number average molecular weight, M_n , of 10,000 to 12,000; and, wherein the high molecular weight polyol curative has an average of 6 hydroxyl groups per molecule; and, 10 to 30 wt % of the difunctional curative; wherein the difunctional curative is a diamine curative selected from the group consisting of 4,4'-methylenebis-(2-chloroaniline) (MBOCA); 4,4'-methylene-bis-(3-chloro-2,6-diethylaniline) (MCDEA); and, isomers thereof; wherein the stoichiometric ratio of the reactive hydrogen groups (i.e., the sum of the amine (NH₂) groups and the hydroxyl (OH) groups) in the curative package to the unreacted isocyanate groups (i.e., NCO groups) in the polyfunctional isocyanate is 0.95 to 1.05; and, wherein the polishing layer exhibits a density of 0.75 to 1.0 g/cm³; a Shore D hardness of 5 to 20; an elongation to break 150 to 300%; and, a cut rate of 30 to 60 μ m/hr.

The present invention also provides a method of making a chemical mechanical polishing pad according to the present invention, comprising: providing a polyfunctional isocyanate; providing a curative package, comprising: (i) providing at least 5 wt % of an amine initiated polyol curative, wherein the amine initiated polyol curative contains at least one nitrogen atom per molecule; wherein the amine initiated polyol curative has an average of at least three hydroxyl groups per molecule; (ii) providing 25 to 95 wt % of a high molecular weight polyol curative, wherein the high molecular weight polyol curative has a number average molecular weight, M_n , of 2,500 to 100,000; and wherein the high molecular weight polyol curative has an average of 3 to 10 hydroxyl groups per molecule; and, (iii) providing 0 to 70 wt % of a difunctional curative; mixing the polyfunctional isocyanate and the curative package to form a combination; and, allowing the combination to react forming a polishing layer.

The present invention provides a method of polishing a substrate, comprising: providing a substrate selected from at least one of a magnetic substrate, an optical substrate and a semiconductor substrate; providing a chemical mechanical polishing pad according to claim 1; creating dynamic contact between a polishing surface of the polishing layer and the

substrate to polish a surface of the substrate; and, conditioning of the polishing surface with an abrasive conditioner.

DETAILED DESCRIPTION

The chemical mechanical polishing pads of the present invention have a polishing layer that exhibits a unique combination of low hardness (i.e., Shore D \leq 40) to provide low defect polishing performance and a low tensile elongation (i.e., elongation to break \leq 450%) which provides both machinability to facilitate the formation of grooves in the polishing layer and conditionability to facilitate the formation of microtexture using a diamond conditioning disk. In addition, the balance of properties enabled by the polishing layer of the present invention provides the ability to, for example, polish semiconductor wafers without damaging the wafer surface by creating micro-scratch defects that could compromise the electrical integrity of the semiconductor device.

The chemical mechanical polishing pad of the present invention for polishing a substrate selected from at least one of a magnetic substrate, an optical substrate and a semiconductor substrate; comprises a polishing layer, wherein the polishing layer comprises the reaction product of raw material ingredients, including: a polyfunctional isocyanate; and, a curative package, comprising: at least 5 wt % (preferably 5 to 30 wt %; more preferably 5 to 25 wt %; most preferably 5 to 20 wt %) of an amine initiated polyol curative, wherein the amine initiated polyol curative contains at least one nitrogen atom per molecule (preferably, wherein the amine initiated polyol curative contains one to four nitrogen atoms per molecule; more preferably, wherein the amine initiated polyol curative contains two to four nitrogen atoms per molecule; most preferably, wherein the amine initiated polyol curative contains two nitrogen atoms per molecule); wherein the amine initiated polyol curative has an average of at least three hydroxyl groups (preferably 3 to 6 hydroxyl groups; more preferably 3 to 5 hydroxyl groups; most preferably 4 hydroxyl groups) per molecule; (preferably wherein the amine initiated polyol curative has a number average molecular weight of \leq 700; more preferably 150 to 650; still more preferably 200 to 500; most preferably 250 to 300); 25 to 95 wt % (preferably 35 to 90 wt %; more preferably 50 to 75 wt %; most preferably 60 to 75 wt %) of a high molecular weight polyol curative, wherein the high molecular weight polyol curative has a number average molecular weight, M_n , of 2,500 to 100,000 (preferably 5,000 to 50,000; more preferably 7,500 to 25,000; most preferably 10,000 to 12,000); and wherein the high molecular weight polyol curative has an average of 3 to 10 hydroxyl groups (preferably 4 to 8 hydroxyl groups; more preferably 5 to 7; most preferably 6) per molecule; and, 0 to 70 wt % (preferably 5 to 60 wt %; more preferably 10 to 50 wt %; still more preferably 10 to 30 wt %; most preferably 10 to 20 wt %) of a difunctional curative; wherein the polishing layer exhibits a density of ≥ 0.6 g/cm³ (preferably, 0.6 to 1.2 g/cm³; more preferably 0.7 to 1.1 g/cm³; most preferably 0.75 to 1.0 g/cm³); a Shore D hardness of 5 to 40 (preferably 5 to 30; more preferably 5 to 20; most preferably 5 to 15); an elongation to break of 100 to 450% (preferably 125 to 425%; more preferably 150 to 300%; most preferably 150 to 200%); and, a cut rate of 25 to 150 μ m/hr (preferably 30 to 125 μ m/hr; more preferably 30 to 100 μ m/hr; most preferably 30 to 60 μ m/hr); and, wherein the polishing layer has a polishing surface adapted for polishing the substrate.

Preferably, the polyfunctional isocyanate used in the formation of the polishing layer of the chemical mechanical polishing pad of the present invention contains two reactive isocyanate groups (i.e., NCO).

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Preferably, the polyfunctional isocyanate used in the formation of the polishing layer of the chemical mechanical polishing pad of the present invention is selected from the group consisting of an aliphatic polyfunctional isocyanate, an aromatic polyfunctional isocyanate and a mixture thereof. More preferably, the polyfunctional isocyanate used in the formation of the polishing layer of the chemical mechanical polishing pad of the present invention is a diisocyanate selected from the group consisting of 2,4-toluene diisocyanate; 2,6-toluene diisocyanate; 4,4'-diphenylmethane diisocyanate; naphthalene-1,5-diisocyanate; tolidine diisocyanate; para-phenylene diisocyanate; xylylene diisocyanate; isophorone diisocyanate; hexamethylene diisocyanate; 4,4'-dicyclohexylmethane diisocyanate; cyclohexanediisocyanate; and, mixtures thereof. Still more preferably, the polyfunctional isocyanate used in the formation of the polishing layer of the chemical mechanical polishing pad of the present invention is an isocyanate terminated urethane prepolymer formed by the reaction of a diisocyanate with a prepolymer polyol.

Preferably, the isocyanate-terminated urethane prepolymer used in the formation of the polishing layer of the chemical mechanical polishing pad of the present invention has 2 to 12 wt % unreacted isocyanate (NCO) groups. More preferably, the isocyanate-terminated urethane prepolymer used in the formation of the polishing layer of the chemical mechanical polishing pad of the present invention has 2 to 10 wt % (still more preferably 4 to 8 wt %; most preferably 5 to 7 wt %) unreacted isocyanate (NCO) groups.

Preferably the prepolymer polyol used to form the polyfunctional isocyanate terminated urethane prepolymer is selected from the group consisting of diols, polyols, polyol diols, copolymers thereof and mixtures thereof. More preferably, the prepolymer polyol is selected from the group consisting of polyether polyols (e.g., poly(oxytetramethylene) glycol, poly(oxypropylene)glycol and mixtures thereof); polycarbonate polyols; polyester polyols; polycaprolactone polyols; mixtures thereof; and, mixtures thereof with one or more low molecular weight polyols selected from the group consisting of ethylene glycol; 1,2-propylene glycol; 1,3-propylene glycol; 1,2-butanediol; 1,3-butanediol; 2-methyl-1,3-propanediol; 1,4-butanediol; neopentyl glycol; 1,5-pentanediol; 3-methyl-1,5-pentanediol; 1,6-hexanediol; diethylene glycol; dipropylene glycol; and, tripropylene glycol. Still more preferably, the prepolymer polyol is selected from the group consisting of polytetramethylene ether glycol (PTMEG); ester based polyols (such as ethylene adipates, butylene adipates); polypropylene ether glycols (PPG); polycaprolactone polyols; copolymers thereof; and, mixtures thereof. Most preferably, the prepolymer polyol is selected from the group consisting of PTMEG and PPG.

Preferably, when the prepolymer polyol is PTMEG, the isocyanate terminated urethane prepolymer has an unreacted isocyanate (NCO) concentration of 2 to 10 wt % (more preferably of 4 to 8 wt %; most preferably 6 to 7 wt %). Examples of commercially available PTMEG based isocyanate terminated urethane prepolymers include Imuthane® prepolymers (available from COIM USA, Inc., such as, PET-80A, PET-85A, PET-90A, PET-93A, PET-95A, PET-60D, PET-70D, PET-75D); Adiprene® prepolymers (available from Chemtura, such as, LF 800A, LF 900A, LF 910A, LF 930A, LF 931A, LF 939A, LF 950A, LF 952A, LF 600D, LF 601D, LF 650D, LF 667, LF 700D, LF 750D, LF 751D, LF 752D, LF 753D and L325); Andur® prepolymers (available from Anderson Development Company, such as, 70APLF, 80APLF, 85APLF, 90APLF, 95APLF, 60DPLF, 70APLF, 75APLF).

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Preferably, when the prepolymer polyol is PPG, the isocyanate terminated urethane prepolymer has an unreacted isocyanate (NCO) concentration of 3 to 9 wt % (more preferably 4 to 8 wt %, most preferably 5 to 6 wt %). Examples of commercially available PPG based isocyanate terminated urethane prepolymers include Imuthane® prepolymers (available from COIM USA, Inc., such as, PPT-80A, PPT-90A, PPT-95A, PPT-65D, PPT-75D); Adiprene® prepolymers (available from Chemtura, such as, LFG 963A, LFG 964A, LFG 740D); and, Andur® prepolymers (available from Anderson Development Company, such as, 8000APLF, 9500APLF, 6500DPLF, 7501DPLF).

Preferably, the isocyanate terminated urethane prepolymer used in the formation of the polishing layer of the chemical mechanical polishing pad of the present invention is a low free isocyanate terminated urethane prepolymer having less than 0.1 wt % free toluene diisocyanate (TDI) monomer content.

Non-TDI based isocyanate terminated urethane prepolymers can also be used. For example, isocyanate terminated urethane prepolymers include those formed by the reaction of 4,4'-diphenylmethane diisocyanate (MDI) and polyols such as polytetramethylene glycol (PTMEG) with optional diols such as 1,4-butanediol (BDO) are acceptable. When such isocyanate terminated urethane prepolymers are used, the unreacted isocyanate (NCO) concentration is preferably 4 to 10 wt % (more preferably 4 to 8 wt %, most preferably 5 to 7 wt %). Examples of commercially available isocyanate terminated urethane prepolymers in this category include Imuthane® prepolymers (available from COIM USA, Inc. such as 27-85A, 27-90A, 27-95A); Andur® prepolymers (available from Anderson Development Company, such as, IE75AP, IE80AP, IE 85AP, IE90AP, IE95AP, IE98AP); and, Vibrathane® prepolymers (available from Chemtura, such as, B625, B635, B821).

The curative package used in the formation of the polishing layer of the chemical mechanical polishing pad of the present invention preferably contains: at least 5 wt % (preferably 5 to 30 wt %; more preferably 5 to 25 wt %; most preferably 5 to 20 wt %) of an amine initiated polyol curative; 25 to 95 wt % (preferably 35 to 90 wt %; more preferably 50 to 75 wt %; most preferably 60 to 75 wt %) of a high molecular weight polyol curative; and, 0 to 70 wt % (preferably 5 to 60 wt %; more preferably 10 to 15 wt %; still more preferably 10 to 30 wt %; most preferably 10 to 20 wt %) of a difunctional curative.

Preferably, the amine initiated polyol curative used in the formation of the polishing layer of the chemical mechanical polishing pad of the present invention contains at least one nitrogen atom per molecule. More preferably, the amine initiated polyol curative used contains one to four (still more preferably two to four; most preferably two) nitrogen atoms per molecule.

Preferably, the amine initiated polyol curative used in the formation of the polishing layer of the chemical mechanical polishing pad of the present invention has an average of at least three hydroxyl groups per molecule. More preferably, the amine initiated polyol curative used has an average of three to six (still more preferably three to five; most preferably four) hydroxyl groups per molecule.

Preferably, the amine initiated polyol curative used in the formation of the polishing layer of the chemical mechanical polishing pad of the present invention has a number average molecular weight, M_n , of ≤ 700 . More preferably, the amine initiated polyol curative used has a number average molecular weight, M_n , of 150 to 650 (still more preferably 200 to 500; most preferably 250 to 300).

Preferably, the amine initiated polyol curative used in the formation of the polishing layer of the chemical mechanical polishing pad of the present invention has a hydroxyl number (as determined by ASTM Test Method D4274-11) of 350 to 1,200 mg KOH/g. More preferably, the amine initiated polyol curative used has a hydroxyl number of 400 to 1,000 mg KOH/g (most preferably 600 to 850 mg KOH/g).

Examples of commercially available amine initiated polyol curatives include the Voranol® family of amine initiated polyols (available from The Dow Chemical Company); the Quadrol® Specialty Polyols (N,N,N',N'-tetrakis (2-hydroxypropyl ethylene diamine)) (available from BASF); Pluracol® amine based polyols (available from BASF); Multanol® amine based polyols (available from Bayer MaterialScience LLC); triisopropanoamine (TIPA) (available from The Dow Chemical Company); and, triethanolamine (TEA) (available from Mallinckrodt Baker Inc.). A number of preferred amine initiated polyol curatives are listed in TABLE 1.

TABLE 1

Amine initiated polyol curative	Number of OH groups per molecule	M _N	Hydroxyl Number (mg KOH/g)
Triethanolamine	3	149	1130
Triisopropanolamine	3	192	877
MULTRANOL® 9138 Polyol	3	240	700
MULTRANOL® 9170 Polyol	3	481	350
VORANOL® 391 Polyol	4	568	391
VORANOL® 640 Polyol	4	352	638
VORANOL® 800 Polyol	4	280	801
QUADROL® Polyol	4	292	770
MULTRANOL® 4050 Polyol	4	356	630
MULTRANOL® 4063 Polyol	4	488	460
MULTRANOL® 8114 Polyol	4	568	395
MULTRANOL® 8120 Polyol	4	623	360
MULTRANOL® 9181 Polyol	4	291	770
VORANOL® 202 Polyol	5	590	475

Without wishing to be bound by theory, in addition to promoting the desired balance of physical properties in the polishing layer produced therewith, it is believed that the concentration of the amine initiated polyol curative used in the curative package also acts to autocatalyze its reaction and the reaction of any difunctional curative in the curative package with the unreacted isocyanate (NCO) groups present in the polyfunctional diisocyanate.

Preferably, the high molecular weight polyol curative used in the formation of the polishing layer of the chemical mechanical polishing pad of the present invention has a number average molecular weight, M_N, of 2,500 to 100,000. More preferably, the high molecular weight polyol curative used has a number average molecular weight, M_N, of 5,000 to 50,000 (still more preferably 7,500 to 25,000; most preferably 10,000 to 12,000).

Preferably, the high molecular weight polyol curative used in the formation of the polishing layer of the chemical mechanical polishing pad of the present invention has an average of three to ten hydroxyl groups per molecule. More preferably, the high molecular weight polyol curative used has an average of four to eight (still more preferably five to seven; most preferably six) hydroxyl groups per molecule.

Preferably, the high molecular weight polyol curative used in the formation of the polishing layer of the chemical mechanical polishing pad of the present invention has a molecular weight that is higher than the molecular weight of the amine initiated polyol curative used in the curative pack-

age; and, has a hydroxyl number that is lower than that of the amine initiated curative used in the curative package.

Examples of commercially available high molecular weight polyol curatives include Specflex® polyols, Voranol® polyols and Voralux® polyols (available from The Dow Chemical Company); Multanol® Specialty Polyols and Ultracel® Flexible Polyols (available from Bayer Material-Science LLC); and Pluracol® Polyols (available from BASF). A number of preferred high molecular weight polyol curatives are listed in TABLE 2.

TABLE 2

	Number of OH groups per molecule	M _N	Hydroxyl Number (mg KOH/g)
15 High molecular weight polyol curative			
Multanol® 3901 Polyol	3.0	6,000	28
Pluracol® 1385 Polyol	3.0	3,200	50
Pluracol® 380 Polyol	3.0	6,500	25
Pluracol® 1123 Polyol	3.0	7,000	24
20 ULTRACEL® 3000 Polyol	4.0	7,500	30
SPECFLEX® NC630 Polyol	4.2	7,602	31
SPECFLEX® NC632 Polyol	4.7	8,225	32
VORALUX® HF 505 Polyol	6.0	11,400	30
MULTRANOL® 9185 Polyol	6.0	3,366	100
25 VORANOL® 4053 Polyol	6.9	12,420	31

Preferably, the difunctional curative used in the formation of the polishing layer of the chemical mechanical polishing pad of the present invention is selected from diols and diamines. More preferably, the difunctional curative used is a diamine selected from the group consisting of primary amines and secondary amines. Still more preferably, the difunctional curative used is selected from the group consisting of diethyltoluenediamine (DETDA); 3,5-dimethylthio-2,4-toluenediamine and isomers thereof; 3,5-diethyltoluene-2,4-diamine and isomers thereof (e.g., 3,5-diethyltoluene-2,6-diamine); 4,4'-bis-(sec-butylamino)-diphenylmethane; 1,4-bis-(sec-butylamino)-benzene; 4,4'-methylene-bis-(2-chloroaniline); 4,4'-methylene-bis-(3-chloro-2,6-diethylaniline) (MCDEA); polytetramethyleneoxide-di-p-aminobenzoate; N,N'-dialkyldiamino diphenyl methane; p,p'-methylene dianiline (MDA); m-phenylenediamine (MPDA); 4,4'-methylene-bis-(2-chloroaniline) (MBOCA); 4,4'-methylene-bis-(2,6-diethylaniline) (MDEA); 4,4'-methylene-bis-(2,3-dichloroaniline) (MDCA); 4,4'-diamino-3,3'-diethyl-5,5'-dimethyl diphenylmethane, 2,2',3,3'-tetrachloro diamine diphenylmethane; trimethylene glycol di-p-aminobenzoate; and mixtures thereof. Most preferably, the diamine curing agent used is selected from the group consisting of 4,4'-methylenebis-(2-chloroaniline) (MBOCA); 4,4'-methylenebis-(3-chloro-2,6-diethylaniline) (MCDEA); and, isomers thereof.

Preferably, the stoichiometric ratio of the reactive hydrogen groups (i.e., the sum of the amine (NH₂) groups and the hydroxyl (OH) groups) in the components of the curative package to the unreacted isocyanate (NCO) groups in the polyfunctional isocyanate is 0.85 to 1.15 (more preferably 0.90 to 1.10; most preferably 0.95 to 1.05).

The polishing layer of the chemical mechanical polishing pad of the present invention optionally further comprises a plurality of microelements. Preferably, the plurality of microelements are uniformly dispersed throughout the polishing layer. Preferably, the plurality of microelements is selected from entrapped gas bubbles, hollow core polymeric materials, liquid filled hollow core polymeric materials, water soluble materials and an insoluble phase material (e.g., mineral oil). More preferably, the plurality of microelements is

selected from entrapped gas bubbles and hollow core polymeric materials uniformly distributed throughout the polishing layer. Preferably, the plurality of microelements has a weight average diameter of less than 150 μm (more preferably of less than 50 μm ; most preferably of 10 to 50 μm). Preferably, the plurality of microelements comprise polymeric microballoons with shell walls of either polyacrylonitrile or a polyacrylonitrile copolymer (e.g., Expancel® from Akzo Nobel). Preferably, the plurality of microelements are incorporated into the polishing layer at 0 to 35 vol % porosity (more preferably 10 to 25 vol % porosity).

The polishing layer of the chemical mechanical polishing pad of the present invention can be provided in both porous and nonporous (i.e., unfilled) configurations. Preferably, the polishing layer of the chemical mechanical polishing pad of the present invention exhibits a density of $\geq 0.6 \text{ g/cm}^3$ as measured according to ASTM D1622. More preferably, the polishing layer of the chemical mechanical polishing pad of the present invention exhibits a density of 0.6 to 1.2 g/cm^3 (still more preferably 0.7 to 1.1 g/cm^3 ; most preferably 0.75 to 1.0 g/cm^3) as measured according to ASTM D1622.

Preferably, the polishing layer of the chemical mechanical polishing pad of the present invention exhibits a Shore D hardness of 5 to 40 as measured according to ASTM D2240. More preferably, the polishing layer of the chemical mechanical polishing pad of the present invention exhibits a Shore D hardness of 5 to 30 (still more preferably 5 to 20; most preferably 5 to 15) as measured according to ASTM D2240.

Polishing layers exhibiting a Shore D hardness of less than 40 typically have very high elongation to break values (i.e., $>600\%$). Materials exhibiting such high elongation to break values reversibly deform when subjected to machining operations, which results in groove formation that is unacceptably poor and texture creation during diamond conditioning that is insufficient. The unique curative package used in the formation of the polishing layer of the chemical mechanical polishing pad of the present invention provides a low hardness coupled with an elongation to break of 100 to 450% as measured according to ASTM D412. Preferably, the polishing layer of the chemical mechanical polishing pad of the present invention exhibits an elongation to break of 125 to 425% (still more preferably 150 to 300%; most preferably 150 to 200%) as measured according to ASTM D412.

Preferably, the polishing layer of the chemical mechanical polishing pad of the present invention exhibits a cut rate of 25 to 150 $\mu\text{m/hr}$ as measured using the method described herein in the Examples. More preferably, the polishing layer of the chemical mechanical polishing pad of the present invention exhibits a cut rate of 30 to 125 $\mu\text{m/hr}$ (still more preferably 30 to 100 $\mu\text{m/hr}$; most preferably 30 to 60 $\mu\text{m/hr}$) as measured using the method described herein in the Examples.

The chemical mechanical polishing pad of the present invention optionally further comprises at least one additional layer interfaced with the polishing layer. Preferably, the chemical mechanical polishing pad optionally further comprises a compressible base layer adhered to the polishing layer. The compressible base layer preferably improves conformance of the polishing layer to the surface of the substrate being polished.

The polishing layer of the chemical mechanical polishing pad of the present invention has a polishing surface adapted for polishing the substrate. Preferably, the polishing surface has macro texture selected from at least one of perforations and grooves. Perforations can extend from the polishing surface part way or all the way through the thickness of the polishing layer. Preferably, grooves are arranged on the polishing surface such that upon rotation of the chemical

mechanical polishing pad during polishing, at least one groove sweeps over the surface of the substrate being polished. Preferably, the polishing surface has macrotexture including at least one groove selected from the group consisting of curved grooves, linear grooves and combinations thereof.

Preferably, polishing layer of the chemical mechanical polishing pad of the present invention has a polishing surface adapted for polishing the substrate, wherein the polishing surface has a macrotexture comprising a groove pattern formed therein. Preferably, the groove pattern comprises a plurality of grooves. More preferably, the groove pattern is selected from a groove design. Preferably, the groove design is selected from the group consisting of concentric grooves (which may be circular or spiral), curved grooves, cross hatch grooves (e.g., arranged as an X-Y grid across the pad surface), other regular designs (e.g., hexagons, triangles), tire tread type patterns, irregular designs (e.g., fractal patterns), and combinations thereof. More preferably, the groove design is selected from the group consisting of random grooves, concentric grooves, spiral grooves, cross-hatched grooves, X-Y grid grooves, hexagonal grooves, triangular grooves, fractal grooves and combinations thereof. Most preferably, the polishing surface has a spiral groove pattern formed therein. The groove profile is preferably selected from rectangular with straight side walls or the groove cross section may be "V" shaped, "U" shaped, saw-tooth, and combinations thereof.

Preferably, the polishing layer used in the chemical mechanical polishing pad of the present invention has an average thickness of 20 to 150 mils. More preferably, the polishing layer used has an average thickness of 30 to 125 mils (still more preferably 40 to 120 mils; most preferably 50 to 100 mils).

Preferably, the method of making a chemical mechanical polishing pad of the present invention, comprises: providing a polyfunctional isocyanate; providing a curative package, comprising: (i) providing at least 5 wt % (preferably 5 to 30 wt %; more preferably 5 to 25 wt %; most preferably 5 to 20 wt %) of an amine initiated polyol curative, wherein the amine initiated polyol curative contains at least one nitrogen atom per molecule (preferably, wherein the amine initiated polyol curative contains one to four nitrogen atoms per molecule; more preferably, wherein the amine initiated polyol curative contains two to four nitrogen atoms per molecule; most preferably, wherein the amine initiated polyol curative contains two nitrogen atoms per molecule); wherein the amine initiated polyol curative has an average of at least three hydroxyl groups (preferably 3 to 6 hydroxyl groups; more preferably 3 to 5 hydroxyl groups; most preferably 4 hydroxyl groups) per molecule; (preferably wherein the amine initiated polyol curative has a number average molecular weight of ≤ 700 ; more preferably 150 to 650; still more preferably 200 to 500; most preferably 250 to 300); (ii) providing 25 to 95 wt % (preferably 35 to 90 wt %; more preferably 50 to 75 wt %; most preferably 60 to 75 wt %) of a high molecular weight polyol curative, wherein the high molecular weight polyol curative has a number average molecular weight, M_n , of 2,500 to 100,000 (preferably 5,000 to 50,000; more preferably 7,500 to 25,000; most preferably 10,000 to 12,000); and wherein the high molecular weight polyol curative has an average of 3 to 10 hydroxyl groups (preferably 4 to 8 hydroxyl groups; more preferably 5 to 7; most preferably 6) per molecule; and, (iii) providing 0 to 70 wt % (preferably 5 to 60 wt %; more preferably 10 to 50 wt %; still more preferably 10 to 30 wt %; most preferably 10 to 20 wt %) of a difunctional curative; mixing the polyfunctional isocyanate and the cura-

tive package to form a combination; and, allowing the combination to react forming a polishing layer.

The method of making a chemical mechanical polishing pad of the present invention, optionally, further comprises: providing a mold; pouring the combination into the mold; and, allowing the combination to react in the mold to form a cured cake; wherein the polishing layer is derived from the cured cake. Preferably, the cured cake is skived to derive multiple polishing layers from a single cured cake. Optionally, the method further comprises heating the cured cake to facilitate the skiving operation. Preferably, the cured cake is heated using infrared heating lamps during the skiving operation in which the cured cake is skived into a plurality of polishing layers.

Preferably, the method of polishing a substrate of the present invention, comprises: providing a substrate selected from at least one of a magnetic substrate, an optical substrate and a semiconductor substrate (preferably a semiconductor substrate; more preferably, a semiconductor substrate, wherein the semiconductor substrate is a semiconductor wafer); providing a chemical mechanical polishing pad according to the present invention; creating dynamic contact between a polishing surface of the polishing layer and the substrate to polish a surface of the substrate; and, conditioning of the polishing surface with an abrasive conditioner.

Some embodiments of the present invention will now be described in detail in the following Examples.

Comparative Examples A-B and Examples 1-19

Polishing layers were prepared according to the formulation details provided in TABLE 3. Specifically, polyurethane cakes were prepared by the controlled mixing of the isocyanate terminated urethane prepolymer at 51° C. (i.e., the Adiprene® LF667 available from for Comparative Example A and Examples 1-9; and, the Adiprene® LFG963A for Comparative Example B and Examples 10-19; both available from Chemtura Corporation) with the components of the curative package. The amine initiated polyol curative (i.e., the Voralux® 800 available from The Dow Chemical Company) and

the high molecular weight polyol curative (i.e., the Voralux® HF505 available from The Dow Chemical Company) were premixed before blending in the other raw materials. All of the raw materials, except for MBOCA, were maintained at a premixing temperature of 51° C. The MBOCA was maintained at a premixing temperature of 116° C. The ratio of the isocyanate terminated urethane prepolymer and the curative package was set such that the stoichiometry, as defined by the ratio of active hydrogen groups (i.e., the sum of the —OH groups and —NH₂ groups) in the curatives to the unreacted isocyanate (NCO) groups in the isocyanate terminated urethane prepolymer, was as noted in Table 3.

Porosity was introduced into the polishing layers by adding Expancel® microspheres to the isocyanate terminated urethane prepolymer prior to combining with the curative package to achieve the desired porosity and pad density.

The isocyanate terminated urethane prepolymer with any incorporated Expancel® microspheres and the curative package were mixed together using a high shear mix head. After exiting the mix head, the combination was dispensed over a period of 5 minutes into a 86.4 cm (34 inch) diameter circular mold to give a total pour thickness of approximately 10 cm (4 inches). The dispensed combination was allowed to gel for 15 minutes before placing the mold in a curing oven. The mold was then cured in the curing oven using the following cycle: 30 minutes ramp from ambient temperature to a set point of 104° C., then hold for 15.5 hours at 104° C., and then 2 hour ramp from 104° C. to 21° C.

The cured polyurethane cakes were then removed from the mold and skived (cut using a moving blade) at a temperature of 30 to 80° C. into approximately forty separate 2.0 mm (80 mil) thick sheets. Skiving was initiated from the top of each cake. Any incomplete sheets were discarded.

Note that Adiprene® LF667 used in the Examples is a PTMEG based isocyanate terminated urethane prepolymer comprising a 50/50 weight percent blend of Adiprene® LF950A and Adiprene® LF600D available from Chemtura. Also note that Adiprene® LFG963A is a PPG based isocyanate terminated urethane prepolymer available from Chemtura.

TABLE 3

Ex #	Isocyanate terminated urethane prepolymer	Prepolymer (% NCO)	Curative Package (wt %)				Expancel ® Pore Former	Former (wt %)	Porosity (vol %)
			MBOCA	Voranol ® 800	Voralux ® HF 505	Stoichiometry (Active H/NCO)			
A	Adiprene ® LF667	6.7	100	0	0	0.85	551DE40d42	1.8	35
B	Adiprene ® LFG963A	5.8	100	0	0	0.9	551DE40d42	1.3	23
1	Adiprene ® LF667	6.7	0	25	75	0.97	920DE40d30	1.3	34
2	Adiprene ® LF667	6.7	67	8	25	0.97	920DE40d30	1.3	34
3	Adiprene ® LF667	6.7	0	14	86	1.0	551DE40d42	1.4	29
4	Adiprene ® LF667	6.7	14	12	74	1.0	551DE40d42	1.4	29
5	Adiprene ® LF667	6.7	25	11	64	1.0	551DE40d42	1.4	28
6	Adiprene ® LF667	6.7	25	11	64	1.0	551DE40d42	0.6	15
7	Adiprene ® LF667	6.7	40	9	51	1.0	551DE40d42	1.4	28
8	Adiprene ® LF667	6.7	50	7	43	1.0	551DE40d42	1.6	32
9	Adiprene ® LF667	6.7	50	7	43	1.0	551DE40d42	0.7	18
10	Adiprene ® LFG963A	5.8	14	12	74	1.0	551DE20d60	2.0	28
11	Adiprene ® LFG963A	5.8	33	10	57	1.0	551DE20d60	2.0	28
12	Adiprene ® LFG963A	5.8	14	12	74	1.0	551DE20d60	1.4	22
13	Adiprene ® LFG963A	5.8	33	10	57	1.0	551DE20d60	1.5	23
14	Adiprene ® LFG963A	5.8	41	8	51	1.0	551DE20d60	1.4	22
15	Adiprene ® LFG963A	5.8	33	10	57	1.0	—	—	—
16	Adiprene ® LFG963A	5.8	0	25	75	1.0	551DE20d60	2.0	28
17	Adiprene ® LFG963A	5.8	0	14	86	1.0	551DE20d60	1.8	26
18	Adiprene ® LFG963A	5.8	25	19	56	1.0	551DE40d42	1.6	32
19	Adiprene ® LFG963A	5.8	25	19	56	1.0	551DE40d42	0.7	17

The ungrooved, polishing layer materials from each of Comparative Examples A-B and Examples 1-19 were analyzed to determine their physical properties as reported in

groove depth over time, based on the collected thickness measurements taken as >2,000 points across the polishing surface of the polishing layer.

TABLE 4

Ex. #	Density (g/cm ³)	Shore Hardness		G' @ 30° C.	G' @ 40° C.	G'' @ 40° C.	G' @30° C./ G' @90° C.	Tensile strength	Elongation to break	Tensile modulus	Toughness	Cut rate
		A	D	(MPa)	(MPa)	(MPa)	(MPa)	(MPa)	(%)	(MPa)	(MPa)	(μm/hr)
A	0.78	93	43	—	44.0	2.6	1.4	17	191	65	24	34
B	0.88	91	41	—	49.0	3.2	1.9	15	293	95	62	26
1	0.76	56	10	3.2	3.1	0.1	1.0	3	161	4	3	—
2	0.76	83	35	27.8	24.2	2.7	1.4	16	250	46	23	—
3	0.81	48	7	2.2	2.2	0.1	1.1	2	160	3	2	72
4	0.81	57	11	4.6	3.8	0.5	1.5	5	294	5	9	41
5	0.82	62	18	9.0	8.2	0.9	1.3	7	360	13	15	—
6	0.98	61	17	5.0	4.6	0.5	1.1	8	414	7	16	—
7	0.82	75	23	16.8	15.6	1.4	1.3	11	346	26	22	30
8	0.79	79	27	21.4	19.7	1.6	1.4	12	332	36	26	29
9	0.95	83	31	23.2	21.5	1.9	1.2	16	351	40	34	—
10	0.83	56	10	6.0	4.5	0.9	2.8	4	189	6	5	46
11	0.82	75	23	18.6	13.4	3.0	6.0	7	256	31	13	—
12	0.90	61	14	8.2	6.4	1.2	3.1	4	164	8	4	—
13	0.88	72	21	18.1	13.8	3.1	5.1	7	288	24	15	—
14	0.89	77	25	23.6	18.7	3.8	5.2	9	291	33	18	43
15	1.14	78	27	21.2	15.6	3.7	4.7	10	293	23	18	—
16	0.83	55	10	5.6	4.5	0.7	2.0	3	162	4	3	—
17	0.85	57	11	4.6	4.0	0.4	1.7	3	143	4	2	—
18	0.78	70	19	18.0	13.3	2.6	4.7	5	173	23	7	—
19	0.96	73	20	17.9	12.5	2.9	5.4	7	232	23	11	—

TABLE 4. Note that the density data reported were determined according to ASTM D1622; the Shore D hardness data reported were determined according to ASTM D2240; the Shore A hardness data reported were determined according to ASTM D2240; and, the elongation to break data reported were determined according to ASTM D412.

The cut rate data reported in TABLE 4 were measured using a 200 mm Mirra® polishing tool from Applied Materials. This polishing tool is designed to accommodate a circular chemical mechanical polishing pad having a nominal diameter of 51 cm (20 inches). Polishing layers having a circular cross section were prepared as described herein in the Examples. These polishing layers were then machine grooved to provide a groove pattern in the polishing surface comprising a plurality of concentric circular grooves having dimensions of 120 mil (3.05 mm) pitch, 20 mil (0.51 mm) width and 30 mil (0.76 mm) depth. The polishing layers were then laminated to a foam sub-pad layer (SP2310 available from Rohm and Haas Electronic Materials CMP Inc.)

A diamond conditioning disk (DiaGrid® AD3CL-150840-3 pad conditioner manufactured by Kinik Company) was used to abrade the polishing surface of the grooved polishing layers using the following process conditions: the polishing surface of the polishing layers were subjected to continuous abrasion from the diamond conditioning disk for a period of 2 hours, with a platen speed of 100 rpm, a deionized water flow rate of 150 cm³/min and a conditioning disk down force of 48.3 kPa (7 psi). The cut rate was determined by measuring the change in the average groove depth over time. The groove depth was measured (in μm/hour) using an MTI Instruments Microtrack II Laser Triangulation Sensor mounted on a Zaber Technologies Motorized Slide to profile the polishing surface of each polishing layer from the center to the outer edge. The sweep speed of the sensor on the slide was 0.732 mm/s and the sampling rate (measurements/mm of sweep) for the sensor was 6.34 points/mm. The cut rate reported in TABLE 4 is the arithmetic average reduction in

We claim:

1. A chemical mechanical polishing pad for polishing a substrate selected from at least one of a magnetic substrate, an optical substrate and a semiconductor substrate; comprising a polishing layer, wherein the polishing layer comprises the reaction product of raw material ingredients, comprising:

a polyfunctional isocyanate; and
a curative package, comprising:

at least 5 wt % of an amine initiated polyol curative, wherein the amine initiated polyol curative contains at least one nitrogen atom per molecule; wherein the amine initiated polyol curative has an average of at least three hydroxyl groups per molecule;

25 to 95 wt % of a high molecular weight polyol curative, wherein the high molecular weight polyol curative has a number average molecular weight, M_{n} , of 2,500 to 100,000; and wherein the high molecular weight polyol curative has an average of 5 to 7 hydroxyl groups per molecule; and

0 to 70 wt % of a difunctional curative;

wherein the polishing layer exhibits a density of greater than 0.6 g/cm³; a Shore D hardness of 5 to 40; an elongation at break of 100 to 450%; and a cut rate of 25 to 150 μm/hr; and, wherein the polishing layer has a polishing surface adapted for polishing the substrate.

2. The chemical mechanical polishing pad of claim 1, wherein the stoichiometric ratio of the reactive hydrogen groups in the curative package to the unreacted isocyanate groups in the polyfunctional isocyanate is 0.85 to 1.15.

3. The chemical mechanical polishing pad of claim 2, wherein the polyfunctional isocyanate is selected from the group consisting of an aliphatic polyfunctional isocyanate, an aromatic polyfunctional isocyanate and a mixture thereof.

4. The chemical mechanical polishing pad of claim 3, wherein the difunctional curative is selected from the group consisting of diol curatives and diamine curatives.

5. The chemical mechanical polishing pad of claim 3, wherein the polyfunctional isocyanate is an isocyanate-terminated urethane prepolymer having 2 to 12 wt % unreacted NCO groups.

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6. The chemical mechanical polishing pad of claim 5, wherein the curative package, comprises:

5 5 to 20 wt % of the amine initiated polyol curative, wherein the amine initiated polyol curative contains two nitrogen atom per molecule; wherein the amine initiated polyol curative has an average of 4 hydroxyl groups per molecule; and wherein the amine initiated polyol curative has a number average molecular weight, M_N , of 200 to 400;

10 50 to 75 wt % of the high molecular weight polyol curative, wherein the high molecular weight polyol curative has a number average molecular weight, M_N , of 10,000 to 12,000; and wherein the high molecular weight polyol curative has an average of 6 hydroxyl groups per molecule;

15 10 to 30 wt % of the difunctional curative; wherein the difunctional curative is a diamine curative selected from the group consisting of 4,4'-methylene-bis-(2-chloroaniline) (MBOCA); 4,4'-methylene-bis-(3-chloro-2,6-diethylaniline) (MCDEA); and isomers thereof;

20 wherein the stoichiometric ratio of the reactive hydrogen groups in the curative package to the unreacted isocyanate groups in the polyfunctional isocyanate is 0.95 to 1.05;

wherein the polishing layer exhibits a density of 0.75 to 1.0 g/cm³; a Shore D hardness of 5 to 20; an elongation at break of 150 to 300%; and a cut rate of 30 to 60 μ m/hr.

7. The chemical mechanical polishing pad of claim 6, wherein the isocyanate-terminated urethane prepolymer has 5 to 7 wt % unreacted NCO groups; and wherein the isocyanate-terminated urethane prepolymer exhibits a number average molecular weight, M_N , of 400 to 2,500.

8. The chemical mechanical polishing pad of claim 7, wherein the polishing surface has a spiral groove pattern formed therein.

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9. A method of making a chemical mechanical polishing pad according to claim 1, comprising:

providing a polyfunctional isocyanate;
providing a curative package, comprising:

(i) providing at least 5 wt % of an amine initiated polyol curative, wherein the amine initiated polyol curative contains at least one nitrogen atom per molecule; wherein the amine initiated polyol curative has an average of at least three hydroxyl groups per molecule;

(ii) providing 25 to 95 wt % of a high molecular weight polyol curative, wherein the high molecular weight polyol curative has a number average molecular weight, M_N , of 2,500 to 100,000; and wherein the high molecular weight polyol curative has an average of 5 to 7 hydroxyl groups per molecule; and

(iii) providing 0 to 70 wt % of a difunctional curative; mixing the polyfunctional isocyanate and the curative package to form a combination; and allowing the combination to react forming a polishing layer.

10. The chemical mechanical polishing pad of claim 1, wherein the high molecular weight polyol curative has a number average molecular weight, M_N , of 7,500 to 25,000.

11. The chemical mechanical polishing pad of claim 1, wherein the polishing layer further comprises a plurality of hollow core polymeric materials.

12. The chemical mechanical polishing pad of claim 11, wherein the plurality of hollow core polymeric materials are uniformly distributed throughout the polishing layer.

13. The chemical mechanical polishing pad of claim 12, wherein the plurality of hollow core polymeric materials have a weight average diameter of 10 to 50 μ m.

14. The chemical mechanical polishing pad of claim 13, wherein the plurality of hollow core polymeric materials are incorporated into the polishing layer at 10 to 25 vol % porosity.

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